Ref #	Hits	Search Query	DBs	Default Operato r	Plural s	Time Stamp
L1	61	high adj K adj dielectric with plasma with etch\$3	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/11/12 14:20
L2	0	1 and gas with etchant with no with plasma	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/11/12 14:18
L3	16	1 and gas with etchant	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/11/12 14:18
L4	4	high adj K adj dielectric with plasma with modify\$3	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/11/12 14:27
L5	3	4 and etch\$4 with gas	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/11/12 14:21

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L6	9	high adj K adj dielectric with plasma adj treatment	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/11/12 14:27
L7	0	6 and non adj plasma adj etch\$3	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/11/12 14:27
L8	111	non adj plasma adj etch\$3	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/11/12 14:27
L9	1	8 and plasma with high adj (k or permittivity)	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/11/12 14:33
L10	1837	438/689.ccls.	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/11/12 14:31

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L11	156	438/722.ccls.	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/11/12 14:32
L12	665	216/58.ccls.	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/11/12 14:32
L13	446	216/63.ccls.	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/11/12 14:32
L14	2942	216/67.ccls.	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/11/12 14:32
L15	132949	Chen.in.	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/11/12 14:33

L16	58	Ludviksson.in.	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/11/12 14:33
L17	13	10 and plasma with high adj (k or permittivity)	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/11/12 14:33
L18	8	11 and plasma with high adj (k or permittivity)	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/11/12 14:33
L19	3	12 and plasma with high adj (k or permittivity)	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/11/12 14:33
L20	1	13 and plasma with high adj (k or permittivity)	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/11/12 14:33

L21	10	14 and plasma with high adj (k or permittivity)	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/11/12 14:33
L22	40	15 and plasma with high adj (k or permittivity)	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/11/12 14:33
L23	2	16 and plasma with high adj (k or permittivity)	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/11/12 14:34
L24	9	17 and gas with etch\$3	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/11/12 14:34
L25	7	18 and gas with etch\$3	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/11/12 14:34

						
L26	3	19 and gas with etch\$3	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/11/12 14:34
L27	1	20 and gas with etch\$3	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/11/12 14:34
L28	8	21 and gas with etch\$3	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/11/12 14:37
L29	15	22 and gas with etch\$3	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/11/12 14:34
L30	1	23 and gas with etch\$3	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/11/12 14:36

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L31	1	24 and gas with etch\$3 with ("without" or no or non) adj plasma	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/11/12 14:38
L32	1	25 and gas with etch\$3 with ("without" or no or non) adj plasma	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/11/12 14:39
L33	1	26 and gas with etch\$3 with ("without" or no or non) adj plasma	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/11/12 14:39
L34	0	27 and gas with etch\$3 with ("without" or no or non) adj plasma	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/11/12 14:39
L35	0	28 and gas with etch\$3 with ("without" or no or non) adj plasma	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/11/12 14:39

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L36	1	29 and gas with etch\$3 with ("without" or no or non) adj plasma	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/11/12 14:39
L37	1	30 and gas with etch\$3 with ("without" or no or non) adj plasma	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/11/12 14:39